Fingerprints of the Strong Interaction between Monolayer MoS₂ and Gold

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ABSTRACT

Gold-mediated exfoliation of MoS₂ has attracted considerable interest in the recent years. A strong interaction between MoS₂ and Au facilitates preferential production of centimeter-sized monolayer MoS₂ with near-unity yield and provides a heterostructure system noteworthy from a fundamental standpoint. However, little is known about the detailed nature of the MoS₂–Au interaction and its evolution with the MoS₂ thickness. Here, we identify specific vibrational and binding energy fingerprints of such strong interaction using Raman and X-ray photoelectron spectroscopy, which indicate substantial strain and charge-transfer in monolayer MoS₂. Near-field tip-enhanced Raman spectroscopy reveals heterogeneity of the MoS₂–Au interaction at the nanoscale, reflecting the spatial non-conformity between the two materials. Far-field micro-Raman spectroscopy shows that this interaction is strongly affected by the roughness and cleanliness of the underlying Au. Our results elucidate the nature of the strong MoS₂–Au interaction and provide guidance for strain and charge doping engineering of MoS₂.

KEYWORDS: monolayer MoS₂, gold, strain, doping, TERS, XPS.

Several groups have recently introduced a method of exfoliating large-area transition metal dichalcogenides (TMDCs) monolayers using gold substrates or sacrificial layers.¹⁻³ For MoS₂ in particular, it is possible to prepare centimeter-sized monolayers due to their preferential, near-unity exfoliation yield and the high quality of natural molybdenite.³ This is a major advancement for mechanical exfoliation, which produces the highest-quality crystals but has been challenging to scale up, unlike the readily scalable chemical vapor deposition or liquid phase-exfoliation that produce lower quality crystals. Gold-mediated mechanical exfoliation has quickly attracted attention and has been utilized in fabrication of flexible gas sensors,⁴ lithography patterning for transistor applications,⁵ and construction of large-area vdW heterostructures.^{6,7} A significant advantage of this method is the polymer-free post-transfer of the gold-exfoliated TMDCs, which leaves their surfaces free from residual contamination.^{2,8}

When bulk MoS₂ is pressed against freshly-deposited Au and peeled off, monolayer MoS₂ crystals with a near-unity yield remain on the Au surface.^{2,3} This was rationalized theoretically, showing that the binding energy between the bottom-most MoS₂ layer and Au is larger than the interlayer equivalent in bulk MoS₂,³ and that both tensile and compressive biaxial strains induced in MoS₂ facilitate preferential monolayer exfoliation in the naturally AB-stacked molybdenite (2H phase in Ramsdell notation).⁹ Cross-sectional scanning transmission electron microscopy and X-ray photoelectron spectroscopy (XPS) confirmed that the MoS₂–Au interaction is of van der Waals (vdW) rather than covalent nature.³ This was corroborated by spectroscopic and electronic studies of gold-exfoliated MoS₂ with the Au removed, which showed that the Raman, photoluminescence, and field-effect transistor responses were qualitatively identical to those of the semiconducting 1H phase of monolayer MoS₂ exfoliated directly onto insulating substrates.^{1,2,5,6} These observations signify that the MoS₂ metallicity endowed by the Au^{3,10} can be reversed after transfer onto another

substrate, significantly increasing the scope of this method to optoelectronics, photovoltaics, and photocatalysis.

Despite these research efforts, little is known about the nature of the strong interaction between MoS₂ and Au, its dependence on the number of MoS₂ layers, and specific effects that the Au brings about in MoS₂. This is most likely due to the lack of reliable measurements directly on the Au substrate. In this study, we reveal the spectroscopic fingerprints of the strong monolayer MoS₂–Au interaction, using Raman spectroscopy and XPS of MoS₂ exfoliated on a range of Au substrates, prepared by magnetron sputtering, electron-beam (e-beam) evaporation, and thermal evaporation. Far-field micro-Raman and micro-XPS of mono- and few-layer MoS₂ on Au reveal additional peaks with differing vibrational frequencies and binding energies, respectively, compared to MoS₂ on an insulating substrate, which are explained by an Au-induced strain and charge doping of the bottom-most MoS₂ layer. These results also suggest heterogeneity of the MoS₂–Au interaction, which is unequivocally confirmed by near-field tip-enhanced Raman spectroscopy (TERS) with 10 nm spatial resolution. Finally, we observe clear correlations of the MoS₂–Au interaction strength with the roughness and cleanliness of the underlying Au, which originate in non-conformality between the two materials.

Micro-Raman Spectroscopy and Micro-XPS of MoS₂ on Au

Monolayer (1L), bilayer (2L), trilayer (3L), and bulk MoS₂ crystals were readily identified due to their high optical contrast (Fig. 1a).¹¹ The far-field micro-Raman spectra of 1L MoS₂ on Au exhibit conspicuous broadening and downshift of the E' mode and splitting of the A₁' mode, in comparison to 1L MoS₂ on SiO₂/Si (Fig. 1b). Lattice deformation (strain) and charge-transfer (doping) are the two main factors influencing Raman frequencies in 1L MoS₂.¹² The effect of strain is more pronounced for the in-plane E' phonon,¹³ while carrier doping has a greater influence on the out-of-plane A₁' phonon.^{14,15} The E' mode broadening and downshift can thus be interpreted as heterogeneous biaxial strain, originating in the lattice mismatch between MoS₂ and Au.¹⁶ The induced change in the frequency of a generic Raman mode M can be estimated as $\delta \omega_{\rm M} = \omega_{\rm M}^0 - \omega_{\rm M} = 2\gamma_{\rm M}\omega_{\rm M}^0 \varepsilon$, where $\omega_{\rm M}^0$ and $\omega_{\rm M}$ are the Raman frequencies of the M mode in unstrained and strained lattices, respectively, $\gamma_{\rm M}$ is the Grüneisen parameter of the M mode, and ε is the biaxial strain.¹²

Since the precise values of zero-strain Raman frequencies in 1L MoS₂ ($\omega_{E'}^0$ and $\omega_{A'_1}^0$) are unknown, we use $\omega_{E'}^{SiO_2/Si} = (385.9 \pm 0.2) \text{ cm}^{-1}$ measured on SiO₂/Si as a reference. The E' mode peak frequency for all the 1L MoS₂/Au samples in this study averages at $\omega_{E'} = (378.2 \pm 0.6) \text{ cm}^{-1}$, which yields $\delta \omega_{E'} = 7.7 \text{ cm}^{-1}$ and implies a tensile strain of $\varepsilon = (1.2 \pm 0.1)\%$ when $\gamma_{E'} = 0.82$ is used (average from refs ^{12,13}). If the observed broadening of the E' mode on Au with a linewidth of $\Gamma_{E'} = (6.1 \pm 0.5) \text{ cm}^{-1}$ were caused solely by heterogeneous lattice deformation, the biaxial tension would fall between 0.6% and 1.9%, taken as 5th and 95th percentiles of the distribution of peaks with $\Gamma_{E'} = 2.4 \text{ cm}^{-1}$ (measured on SiO₂/Si) within the broadened peak.

The average strain-induced downshift of the A₁' mode is $\delta \omega_{A'_1} = (1.7 \pm 0.2) \text{ cm}^{-1}$, calculated using $\varepsilon = 1.2\%$, $\omega_{A'_1}^{\text{SiO}_2/\text{Si}} = (404.0 \pm 0.2) \text{ cm}^{-1}$, and $\gamma_{A'_1} = 0.18.^{12,13}$ However, the A₁' mode is visibly split into two components (Fig. 1b), which we define as the lower frequency $A_{1'}(L)$ mode at (396.4 ± 0.3) cm⁻¹ and the higher frequency $A_{1'}(H)$ mode at (403.7 ± 0.2) cm⁻¹, corresponding to $\delta \omega_{A'_{1}(L)} = 7.6$ cm⁻¹ and $\delta \omega_{A'_{1}(H)} = 0.3$ cm⁻¹. The most probable origin of the highly downshifted $A_{1'}(L)$ component is the substrate-induced doping, which affects a portion of the 1L MoS₂. The net $A_{1'}(L)$ shift $\delta \omega_{A'_{1}(L)}^{corr} = 5.9$ cm⁻¹, corrected for the strain by subtracting 1.7 cm⁻¹, implies n-type doping of MoS₂ and electron concentration estimate of $n_e \sim 2.6 \times 10^{13}$ cm⁻² for $A_{1'}(L)$,^{14,17} Conversely, the strain-corrected net $A_{1'}(H)$ shift, $\delta \omega_{A'_{1}(H)}^{corr} = -1.4$ cm⁻¹, points to an electron withdrawal. Since the SiO₂/Si reference is known to induce n-doping in MoS₂,^{18,19} it suggests that $A_{1'}(H)$ corresponds to regions of undoped MoS₂ without a direct contact to Au.

The broadening and splitting of the E' and A_1 ' Raman modes suggest that the MoS_2 –Au interaction is heterogeneous, which leads to a multitude of strain and doping states of the MoS_2 and results in the convoluted multi-component spectral response observed in Fig. 1b–c. In the extreme case of the top spectrum in Fig. 1b (100 nm Au peeled), the dominating low frequency component E'(L) is accompanied by a high frequency shoulder E'(H), the presence of which is correlated with the A_1 '(H) intensity, as discussed below.

The evolution of the Raman spectra with the number of MoS_2 layers shown in Fig. 1c for the Au (15 nm e-beam) and SiO₂/Si substrates brings further clarity. It transpires that only the bottom-most MoS_2 layer interacts strongly with the adjacent Au substrate, while the top layers in 2L, 3L, and bulk MoS_2 , without a direct contact to Au, are only partially strained and virtually undoped (see also Fig. 4a). We arrive at this conclusion since E'(L) and A₁'(L) are replicated in the thicker layers also, with their frequencies and absolute intensities maintained. These components are readily resolved in 2L, less so in 3L, and negligible in bulk, due to the increased intensities of E'(H) and A₁'(H) (Fig. 1c). Note, that the notation of the Raman modes in MoS_2 is layer-dependent due to symmetry considerations. Thus, E' and A_1 ' versus E_{2g}^1 and A_{1g} irreducible representations are used for an odd number of layers versus even number of layers and bulk.²⁰

The biaxial strain and doping observed above are among the highest observed to date.^{10,13-15,17,21-23} Previous Raman studies of the MoS₂/Au heterostructures either deal with a weak MoS₂–Au interaction, are unable resolve the individual spectral components, or offer limited discussion of their origin. Upshifts of both the E'/E_{2g}^1 and A_1'/A_{1g} modes with the MoS₂ thickness were observed using a low-resolution spectrometer,^{3,11} consistent with Fig. 1c if heavily averaged spectra are considered. A downshift of E' to 381 cm⁻¹ assigned to strain and an undiscussed low-frequency shoulder near A_1' at 399 cm⁻¹ were reported recently.¹⁰ A broadening and downshift of E' to 379 cm⁻¹ due to strain and upshift of the A_1' mode explained by stiffening of the out-of-plane vibration, was observed for 1L MoS₂ with the Au deposited on top.¹⁶ This corresponds with the behavior of A_1' (H) in our study, but contradicts the appearance of A_1' (L).

Both n- and p-type doping of MoS₂ interacting with Au have been reported,^{10,24,25} probably due to the broad range of work functions (Φ), dependent on preparation, thickness, and surface conditions ($\Phi_{Au} \sim 4.8 - 5.4 \text{ eV}$,^{26,27} $\Phi_{MoS_2} \sim 4.0 - 5.4 \text{ eV}^{28,29}$). This means that the difference $\Delta \Phi$ = $\Phi_{MoS_2} - \Phi_{Au}$ can take both signs. From the ultraviolet photoelectron spectroscopy (UPS) in Supporting Fig. S1 and Kelvin probe force microscopy (KPFM) in Supporting Fig. S2, we estimate $\Delta \Phi$ to be ~0.3-0.2 eV, confirming the net n-type doping of MoS₂ induced by the Au.

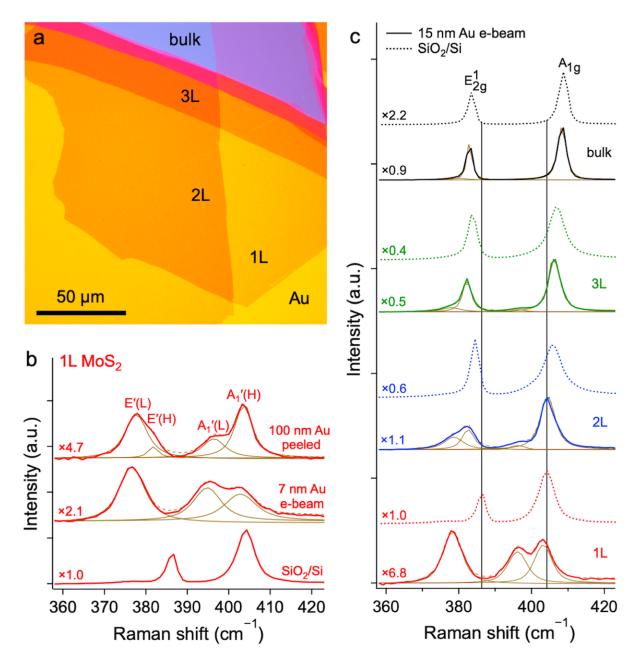


Figure 1. Far-field micro-Raman spectra of MoS₂ **on Au. a,** Optical image of MoS₂ exfoliated on Au (15 nm e-beam). b, Raman spectra of monolayer MoS₂ on different substrates: SiO₂/Si, 7 nm e-beam Au, and 100 nm thermal Au peeled from Si. **c,** Raman spectra of 1L, 2L, 3L, and bulk MoS₂ on 15 nm e-beam Au (solid) and SiO₂/Si (dotted). Spectra were collected using a 532 nm excitation and normalized to their highest peaks with the corresponding multiplicators shown on the left. Curve fittings using the Voigt function are shown in brown.

Fig. 2 shows the high-resolution micro-XPS data for the Mo 3d and S 2p core levels, obtained from 1L, 2L, 3L, and bulk MoS₂. Photoemission electron microscopy (PEEM) images of the sampled areas are shown in the insets. The Mo 3d and S 2p peaks in 1L are asymmetric and their fitting with two Voigt doublets yields a good match with the spectra, revealing a chemical shift of ~0.4 eV between the higher (H) and lower (L) binding energy components, which appear to have the same origin as $A_1'(L)$ and $A_1'(H)$ in the 1L Raman spectra (Fig. 1b–c), respectively. The upshift (downshift) of H (L) in 1L from the dominant L component in 2L and 3L (vertical lines) reflects the Fermi level upshift (downshift) in 1L MoS₂ due to electron injection (withdrawal). This provides further evidence of the suspected heterogeneity of the MoS₂–Au interaction, with n-doped MoS₂ in contact with Au (H) and undoped MoS₂ detached from Au (L). The H components are also partially replicated in the thicker layers, in analogy to $A_1'(L)$ in the Raman spectra of Fig. 1c.

The core level peak energies in bulk MoS_2 are less reliable and burdened by larger uncertainties stemming from the weak Au $4f_{7/2}$ signal used as an internal calibration reference, effects of finite probing depth and charging, and presence of step-edges.³⁰ Importantly, despite the observed shifts in the XPS binding energies and Raman frequencies, the spectral responses are fully consistent with the thermodynamically stable semiconducting 1H phase of 1L MoS_2 ,^{3,10} rather than the unstable metallic 1T' phase observed elsewhere.^{31,32} This important conclusion demonstrates that the lattice symmetry of 1L MoS_2 is preserved and that the Au-induced metallicity can be fully reversed after a transfer onto an insulating substrate.^{2,5}

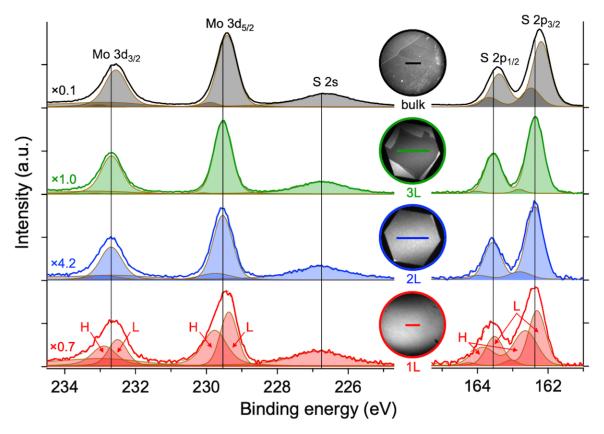


Figure 2. Micro-XPS of MoS_2 on Au. Mo 3d (left) and S 2p (right) core level spectra for 1L, 2L, 3L, and bulk MoS_2 on Au (15 nm e-beam). Normalization and fitting, qualitatively similar to that of in Fig. 1, were applied. The insets show the PEEM images of the measured areas with 30 μ m scale bars.

Nanoscale Heterogeneity of MoS₂ Revealed by TERS

Near-field TERS with 10 nm spatial resolution allowed us to isolate the $A_1'(L)$ and $A_1'(H)$ components in the Raman spectra of 1L MoS₂ on Au. The optical image in Fig. 3a shows the region used for the TERS mapping in Fig. 3b. The spectra from two individual adjacent (10×10) nm^2 pixels shown in Fig. 3c differ greatly and can be matched with the response of 1L MoS₂ strongly (S in red) and weakly (W in blue) interacting with the Au. The S spectrum features only $A_1'(L)$, while the W spectrum is dominated by $A_1'(H)$ with a small $A_1'(L)$ shoulder. The blue patches in a larger red region in the right-hand portion of Fig. 3b therefore indicate the presence of weakly interacting nanoscale inclusions in a strongly interacting 1L MoS₂ sheet, which appears homogeneous in an optical microscope. TERS signals summed over the pure weakly interacting bilayer (W–2L), pure strongly interacting monolayer (S), and mixed (S+W) regions of the map, shown as solid curves in Fig. 3d, corroborate this conclusion. The mixed region response in particular (magenta in Fig. 3d), is in excellent agreement with the far-field Raman spectrum (dotted curve) recorded in the same region. Unreliability of the absolute intensities in fast TERS mapping make the differentiation between the signals from 2L and weakly interacting 1L challenging. We therefore cannot rule out a disruption of the preferential 1L exfoliation by locally weakened MoS₂-Au interaction, potentially leading to nanoscale traces of 2L. In fact, indication of such a phenomenon, with 2L inclusions in a continuous sheet of 1L, was occasionally observed at the microscale (Fig. 3e).

However, a direct proof of the 1L origin of the weakly interacting Raman features is demonstrated by a series of TERS measurements in Fig. 3f, which were acquired using a variable contact tip force on 1L MoS₂ transferred onto 50 nm sputtered Au using a polydimethylsiloxane stamp. As no attention was paid to the freshness and cleanliness of the MoS₂ and Au surfaces in this case, a layer of contamination was trapped between the two materials, through which we were able to push the TERS tip to alter the distance between the MoS_2 and Au, as shown in the inset of Fig. 3f. The top spectrum in Fig. 3f corresponds to the weakly interacting 1L MoS_2/Au heterostructure with $A_1'(H)$ present but $A_1'(L)$ missing. As the tip force increases and the MoS_2 is pressed against the Au, their interaction is strengthened and $A_1'(L)$ begins to appear at the expense of the $A_1'(H)$ intensity.

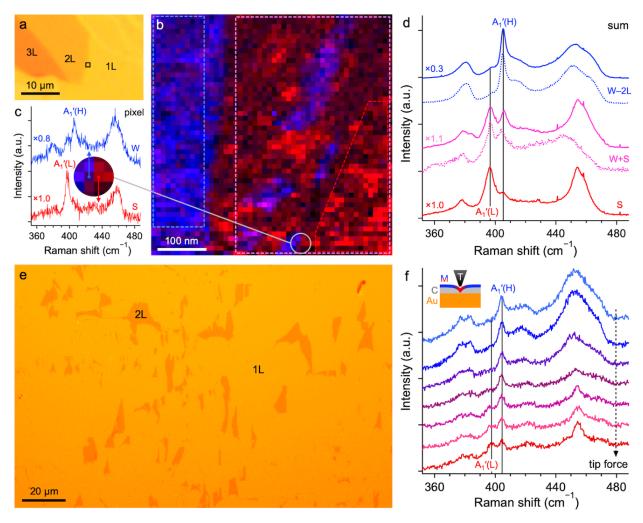


Figure 3. High-resolution TERS of MoS₂ on Au. a, Optical image of MoS₂ on Au (50 nm ebeam). b, TERS map (633 nm excitation) of an interface between 1L and 2L defined in a by a black rectangle. Red, blue, and magenta hues correspond to the intensities of $A_1'(L)$, $A_1'(H)$, and both components, respectively. c, Single-pixel (10×10) nm² TERS of the adjacent strongly (S) and weakly (W) interacting 1L MoS₂. d, TERS summed over the weakly interacting 2L (W–2L), strongly interacting 1L (S), and mixed regions (S+W), from areas highlighted in b by dashed polygons of matching colors. Corresponding far-field Raman spectra (633 nm excitation) are shown as dotted curves. e, Optical image of microscale 2L inclusions in 1L MoS₂. f, TERS acquired with a variable tip force in order to alter the MoS₂–Au interaction. The inset illustrates how the tip (T) pushes the MoS₂ (M) closer to the Au through a layer of contamination (C).

The Effects of Surface Morphology on Raman Vibrations of MoS₂

A detailed analysis of the far-field Raman data reveals several interesting correlations. Fig. 4a summarizes the evolution of the E'/E_{2g}^1 and A_1'/A_{1g} Raman frequencies with the number of MoS₂ layers, for all the Au (color) and SiO₂/Si (gray) substrates. The $A_1'(H)$ component on Au upshifts with increasing number of layers the same way A_1'/A_{1g} does on SiO₂/Si.^{33,34} In contrast, the $A_1'(L)$ component maintains its frequency for 1L–3L, which evidences its origin in the strongly interacting regions of the bottom-most MoS₂ layer.

Fig. 4b shows that the ratio between the $A_1'(L)$ and $A_1'(H)$ intensities of 1L MoS₂ [$A_1'(L)/A_1'(H)$], proportional to the strength of the MoS₂–Au interaction, is strongly correlated with the Au roughness determined by the atomic force microscopy (AFM). This supports the intuitive expectation that the increased conformity of MoS₂ to smoother Au surfaces increases strength of their interaction, as schematically depicted in the Fig. 4b insets. In Fig. 4c, we show that $A_1'(L)/A_1'(H)$ decreases exponentially with the time of Au exposure to air prior to the MoS₂ exfoliation. This further evidences the weakening of the MoS₂–Au interaction due to airborne contamination (see Fig. 4c insets), in agreement with the observed complete suppression of the initially near-unity 1L yield after 15–20 min of Au exposure to air.³ For freshly-made Au (day 0), $A_1'(L)/A_1'(H)$ does not depend on the time elapsed between the Raman measurement and MoS₂ exfoliation, in contrast to aged Au (day 7 and 28).

AFM images of the 1L MoS₂/Au heterostructure in Fig. 4d–f show signs of MoS₂ being suspended between the nanocrystalline features on the Au surface, with a good (poor) contact at the protrusions (depressions). As the Au roughness increases, larger areas of MoS₂ decouple from the substrate, which is reflected by the increased intensity of the weakly interacting $A_1'(H)$ component (insets of Fig. 4b). Larger proportion of suspended MoS₂ with a weak MoS₂–Au interaction also leads to a relative increase in the E'(H) intensity, as seen for the roughest Au substrate in Fig. 1b (top spectrum). The proportional increase of the strongly interacting MoS_2 –Au regions through an increased contact area is further evidenced by an Au/MoS₂/Au "sandwich" prepared by covering 1L MoS₂ on 15 nm Au with another layer of 5 nm Au. This leads to a 40% increase in A₁'(L)/A₁'(H) indicated by the gray-filled marker in Fig. 4b.

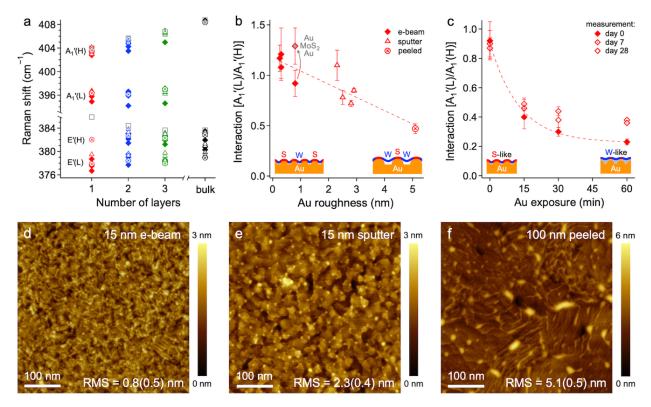


Figure 4. The effects of surface morphology on Raman vibrations of MoS₂. a, Raman frequencies as a function of the number of MoS₂ layers for all measured samples. b, A₁'(L)/A₁'(H) as a function of the Au roughness, determined by AFM. In comparison, the average roughness of 1L MoS₂ was (0.4 ± 0.1) nm. The gray-filled marker corresponds to the 5 nm Au/1L MoS₂/15 nm Au "sandwich". c, A₁'(L)/A₁'(H) as a function of the Au exposure to air prior to the MoS₂ exfoliation (0, 15, 30, 60 min), measured at different times after sample preparation (day 0, 7, 28). Diamond, triangle, circle, and square markers in **a–c**, obtained using the Voigt fitting of the spectra, denote the e-beam Au, sputtered Au, peeled Au, and SiO₂/Si substrates, respectively. **d–f**, AFM images of 1L MoS₂ on 15 nm e-beam, 15 nm sputter, and 100 nm peeled Au, respectively, noting the root mean square roughness (RMS) of the Au (MoS₂) surface.

Origin of the A_1 *' mode splitting*

The experimental evidence presented in this study unequivocally links the appearance of the downshifted $A_1'(L)$ Raman mode to that portion of 1L MoS₂, which strongly interacts with its Au substrate. The n-doping of 1L MoS₂ in contact with Au, proven by XPS, UPS, and KPFM, corroborates that the increased electron concentration is responsible for the A1'(L) downshift, in line with electrochemically-gated MoS₂ experiments.^{14,15,17} Nevertheless, one could envisage alternative explanations. The strong binding in MoS₂-Au heterostructure with a clean interface could cause softening of the Mo-S bonds, instead of the stiffening seen for contaminated MoS₂-Au interface or bulk MoS₂.^{16,33} Alternatively, the strong interaction could lead to activation of phonons otherwise silent in 1L MoS₂, such as those present in multilayer systems.^{34,35} However, this option can be ruled out for A1'(L), since the activation of another mode would not lead to a disappearance of the original A₁', in contrast to our TERS results. We also examined a 1L WS₂/Au heterostructure prepared by the same technique and observed the same apparent splitting of A1' into $A_1'(L)$ and $A_1'(H)$ in the far-field Raman spectra, with the $A_1'(L)$ downshifted by ~7 cm⁻¹ (Supporting Fig. S3). This is a nearly identical shift to that for 1L MoS₂, which clearly points to an electron density increase rather than activation of a new mode.

CONCLUSIONS

We studied Raman spectroscopy and XPS of MoS₂ on gold and identified the specific vibrational and binding energy fingerprints of the strong MoS₂-Au interaction. Far-field micro-Raman reveals significant downshift and broadening of the in-plane E' mode of 1L MoS₂ on Au, compared to MoS₂ on SiO₂/Si, which corresponds to heterogeneous tensile biaxial strains of up to 1.9%. Splitting of the out-of-plane A₁' mode of 1L MoS₂ into two separate components implies that a portion of MoS₂ in close contact with Au experiences n-type charge transfer doping with electron concentrations up to 2.6×10^{13} cm⁻², while another portion of MoS₂ is suspended and remains undoped. This is supported by splitting in the XPS of the Mo 3d and S 2p core levels. The evolution of the micro-Raman spectra and XPS with the MoS₂ thickness confirms that the strong MoS₂-Au interaction is confined to the bottom-most MoS₂ layer. High-resolution TERS mapping confirms the suspected nanoscale heterogeneity of the MoS₂-Au interaction caused by the spatial non-conformity between the two materials. Finally, the micro-Raman data show that the MoS₂-Au interaction can be effectively tuned by the surface morphology and cleanliness of the underlying Au substrate, which could be exploited for strain and charge doping engineering of MoS₂ and utilization of the induced metallicity of gold-exfoliated TMDCs in catalysis.

METHODS

Sample Preparation

Gold films on 90 nm SiO₂/Si wafers (IDB Technologies Ltd) were prepared by three different methods: magnetron sputtering (CMS-A, Kurt J Lesker Company Ltd), e-beam evaporation (SC4500, CVC Products Inc), and thermal evaporation (DV502-A, Denton Vacuum Inc) followed by peeling from a sacrificial Si substrate.⁸ Au thicknesses ranging from 3 to 100 nm were prepared, and an adhesion layer of 1 nm or 3 nm Ti was employed for the sputtered and e-beam samples, respectively. MoS₂ was exfoliated onto the Au surface from bulk molybdenite crystals (Manchester Nanomaterials Ltd), using a low-stain tape.

Characterization

The exfoliated MoS₂ was inspected, and its thickness determined, using a Nikon L200N Eclipse optical microscope. MFP-3D AFM (Asylum Research) in tapping mode was used to determine the surface roughness. An Icon Dimension AFM (Bruker Corp.) in PeakForce tapping mode using Scanasyst-Air probes was employed for the high-resolution characterization of the surface. Far-field Raman spectra were collected using an inVia Reflex confocal spectrometer (Renishaw plc) with a 532 nm laser and 2400 l/mm grating and LabRAM HR (Horiba Ltd) with a 633 nm laser and 1800 l/mm grating, focused to ~1 μ m² spot size by a 100× objective. Near-field TERS was measured using a LabRAM Nano system comprised of HR Evolution spectrometer and OmegaScope-R SPM (HORIBA Scientific) with a 633 nm laser, 1800 l/mm grating, and Agcoated Si tips (App Nano), using 1 s (3 s) integration time for mapping (tip force) measurements, respectively, and <300 μ W laser power for each pixel. XPS, UPS and PEEM were measured in NanoESCA microscope (Omicron). The XPS was collected using a monochromated Al K α source (h ν = 1486.7 eV), and the UPS was carried out using He I discharge lamp (h ν = 21.2 eV). The XPS calibration was done using the Au 4f γ ₂ core level at 84 eV along with the Fermi level edge.

ASSOCIATED CONTENT

Supporting Information:

The Supporting Information is available free of charge on the ACS Publication website at DOI:

Work function estimation from UPS; work function estimation from KPFM; Raman spectra of 1L WS₂ on Au.

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ACKNOWLEDGEMENTS

This project has received funding from the European Union's Horizon 2020 research and innovation program under the Marie Skłodowska-Curie grant agreement No. 746685 and Czech Science Foundation project GACR 17-18702S. This work was performed in part at the Cornell NanoScale Science & Technology Facility, a member of the National Nanotechnology Coordinated Infrastructure, which is supported by the NSF (Grant NNCI-1542081), and made use of the Cornell Center for Materials Research Shared Facilities, which are supported through the NSF MRSEC program (DMR-1719875). This work was also supported by the Ministry of Education, Youth and Sports of the Czech Republic and The European Union - European Structural and Investments Funds in the frame of Operational Programme Research Development and Education project Pro-NanoEnviCz (Reg. No. CZ.02.1.01/0.0/0.0/16_013/0001821). Photoemission spectroscopy experiments were supported by MEYS of the Czech Republic through project CZ.02.1.01/0.0/0.0/16 013/0001406.

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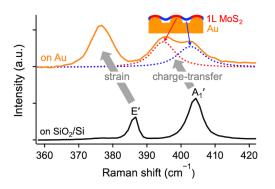
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Table of Contents (TOC):



Supporting Information

Fingerprints of the Strong Interaction between Monolayer MoS₂ and Gold

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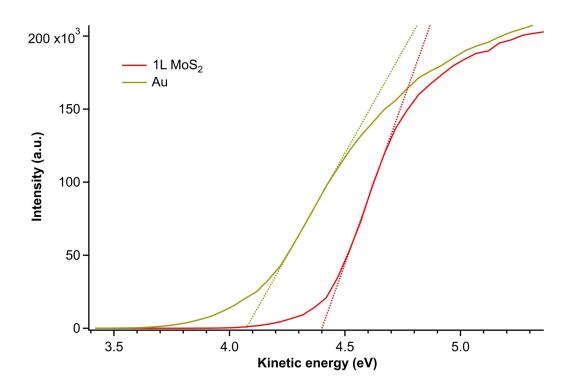
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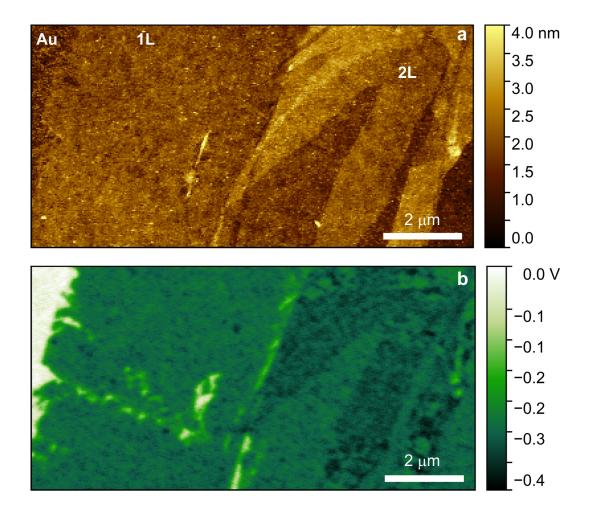
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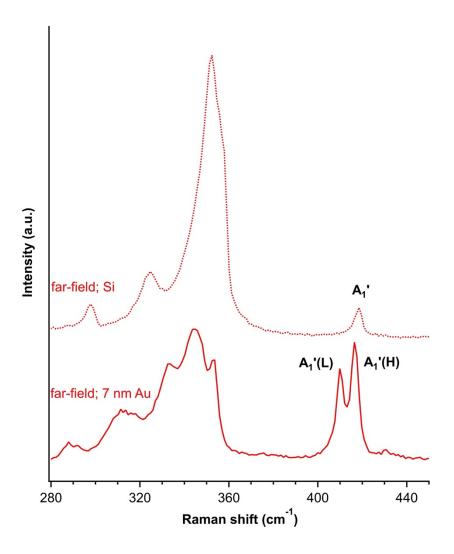
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Supporting Figure S1. Work function estimation using ultraviolet photoelectron spectroscopy. Low kinetic energy cut-off spectra of 1L MoS₂ on Au (solid red; 15 nm e-beam) and of bare Au substrate (solid green) measured next to the MoS₂, with the linear fits (dashed) through the inflection points of the curves. The work function (Φ) is determined from the value of the fitted line at zero intensity. Φ_{MoS_2} was found to be ~0.3 eV larger in comparison to Φ_{Au} . Although the absolute Φ values are burdened with an uncertainty due to the spectrometer response, their difference yields a reliable work function difference estimate.



Supporting Figure S2. Work function estimation using Kelvin probe force microscopy. a, Topography atomic force microscopy image of an area containing 1L and 2L MoS₂ and the bare Au substrate (50 nm e-beam). b, Contact potential difference (CPD) map of a obtained by Kelvin probe force microscopy. The CPD of 1L MoS₂ is lower, and therefore its Φ is larger, than that of the Au substrate. The corresponding difference in the CPD of the two materials, averaged over the whole measured area, is 0.22 V. The trend of increasing work function (decreasing CPD) with the number of layers observed here for 1L/2L MoS₂ is consistent with other literature observations.^{1,2}



Supporting Figure S3. Raman spectra of 1L WS₂. Far-field micro-Raman spectra of 1L WS₂ on 7 nm sputtered Au (bottom curve) and on Si/SiO₂ (top curve), collected using 532 nm excitation.

Supporting References

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